GL610T

Ultra-compact Chip Part Type Infrared Emitting Diodes

■ Features

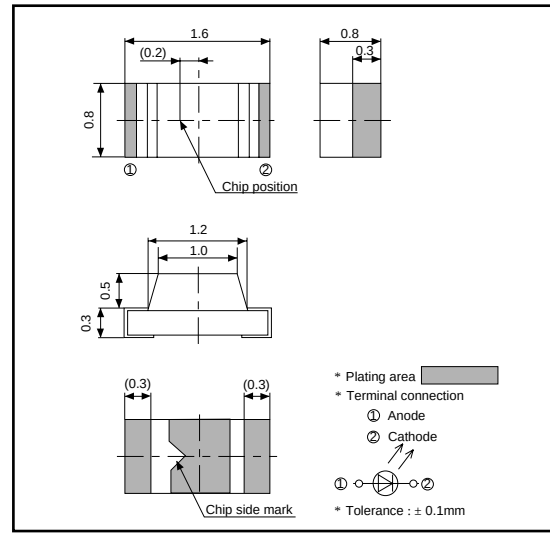
1. Ultra-compact type (1.6 x 0.8 x 0.8 mm)
2. Thin type (thickness : 0.8 mm)
3. Taped-packed type (4,000 pieces/reel)
4. Leadless type

■ Applications

1. Compact and thin remote controllers
2. Tape end detection of VCRs and VCR cameras
3. Power source for car navigator touch panels
4. Other portable equipment

■ Outline Dimensions

(Unit : mm)



■ Absolute Maximum Ratings

(Ta=25˚C)

Parameter	Symbol	Rating	Unit
Forward current	I_F	50	mA
*1 Peak forward current	I_{FM}	500	mA
Reverse voltage	V_R	6	V
Power dissipation	P	150	mW
Operating temperature	T_{opr}	- 25 to + 85	˚C
Storage temperature	T_{stg}	- 25 to + 100	˚C
*2 Soldering temperature	T_{sol}	260	˚C

*1 Pulse width <= 100μ s, Duty ratio=0.01

*2 Hand soldering temperature, for MAX. 3 seconds

■ Electro-optical Characteristics

(Ta=25 ˚C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Forward voltage	V_F	I_F = 50mA	-	1.3	1.5	V
*1 Peak forward voltage	V_{FM}	I_{FM} = 0.5A	-	2.2	3.5	V
Reverse current	I_R	V_R = 3V	-	-	10	μ A
Radiant flux	Φ_e	I_F = 20mA	0.7	2.0	-	mW
Peak emission wavelength	λ_p	I_F = 20mA	-	950	-	nm
Half intensity wavelength	$\Delta\lambda$	I_F = 20mA	-	40	-	nm
Response frequency	f_c	-	-	300	-	kH z
Half intensity angle	$\Delta\theta$	I_F = 20mA	-	± 60	-	˚